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INT.CL.

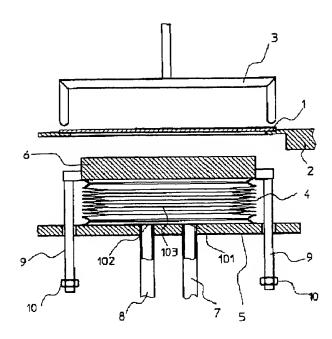
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TITLE

: SEMICONDUCTOR PRODUCING

**DEVICE** 



PURPOSE: To rapidly lower the temp. of a substrate by deforming a flexible member to bring a block fixed to the tip of the flexible member into contact with the substrate just coated with a film.

CONSTITUTION: A substrate 1 is set on a substrate holder 2, heated and coated with a film. The substrate 1 is introduced into a cooling chamber. An inert gas is blown into the closed space 103 of a free-to-expand bellows 4 from a gas inlet 101, hence the bellows 4 is expanded by the gas pressure to push up a block 6 fixed to the tip of the bellows 4, and the block is abutted on the substrate 1. The gas is constantly supplied from the inlet 101, exhausted from an outlet 102 and allowed to cool the substrate 1 through the block 6. The substrate just coated with a film having a uniform composition distribution is rapidly cooled, and the state immediately after the film is formed is maintained. An insulating film having an excellent electrical characteristic is formed in this way.

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